



Dimensions are in inch [metric] units.

FEATURES

- Ideal for electron detection
- Circular active area
- 100% internal QE

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C (PER ELEMENT)

| PARAMETERS | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|----------------------------------|-----------------------------------|------|------|------|-----------------|
| Active Area (per element) | | | 36.5 | | mm ² |
| Responsivity, \mathcal{R} | (see graphs on the next page) | 0.07 | 0.08 | 0.09 | A/W |
| Shunt Resistance, R_{sH} | $V_R = \pm 10\text{mV}$ | 10 | | | MOhms |
| Reverse Breakdown Voltage, V_R | $I_R = 1\mu\text{A}$ | 5 | | | Volts |
| Capacitance, C | $V_R = 0\text{V}$ | | 1.5 | | nF |
| Rise Time | $V_R = 2\text{V}, R_L = 50\Omega$ | | | 2 | usec |

THERMAL PARAMETERS

| STORAGE AND OPERATING TEMPERATURE RANGE | |
|---|---------------------------|
| Ambient ¹ | -10° TO 40°C ¹ |
| Nitrogen or Vacuum | -20°C TO 80°C |
| Maximum Junction Temperature | 70°C |
| Lead soldering temperature ² | 260°C |

¹Temperatures exceeding these parameters may create oxide growth on the active area. Over time responsivity to low energy radiation and wavelengths below 150nm will be compromised.

²0.080" from case for 10 seconds.

Shipped with temporary cover to protect photodiode and wire bond.
Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.



